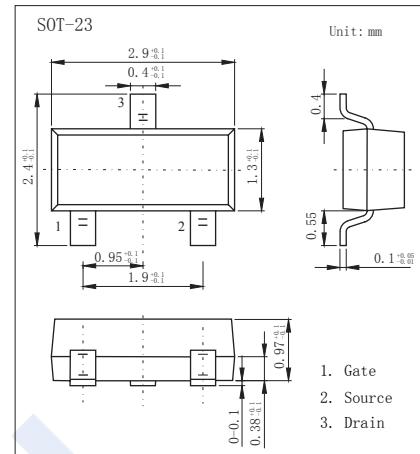
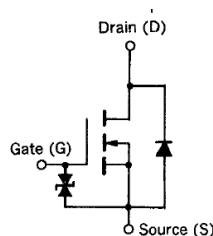


N-Channel MOSFET

2SK1581

■ Features

- V_{DS} (V) = 16V
- I_D = 0.2 A
- $R_{DS(ON)} < 5 \Omega$ ($V_{GS} = 2.5V$)
- $R_{DS(ON)} < 3 \Omega$ ($V_{GS} = 4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	16	V
Gate-Source Voltage	V_{GS}	± 16	
Continuous Drain Current	I_D	200	mA
Pulsed Drain Current (Note.1)	I_{DM}	400	
Power Dissipation $T_a = 25^\circ C$	P_D	200	mW
Junction Temperature	T_J	150	$^\circ C$
Operating Temperature	T_{opt}	-55 to 80	
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: PW \leqslant 10ms, Duty Cycle \leqslant 50%

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250 \mu A, V_{GS}=0V$	16			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GS}	$V_{DS}=0V, V_{GS}=\pm 3V$			± 5	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS}=3V, I_D=10\mu A$	0.8		1.6	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=1m A$			5	Ω
		$V_{GS}=4V, I_D=1m A$			3	
Forward Transconductance	g_{FS}	$V_{DS}=3V, I_D=10m A$	20	70		mS
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=3V, f=1MHz$		27		pF
Output Capacitance	C_{oss}			37		
Reverse Transfer Capacitance	C_{rss}			8		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS(on)}=3V, V_{DS}=3V, I_D=10mA, R_L=300 \Omega, R_G=10 \Omega$		100		ns
Turn-On Rise Time	t_r			300		
Turn-Off Delay Time	$t_{d(off)}$			210		
Turn-Off Fall Time	t_f			240		

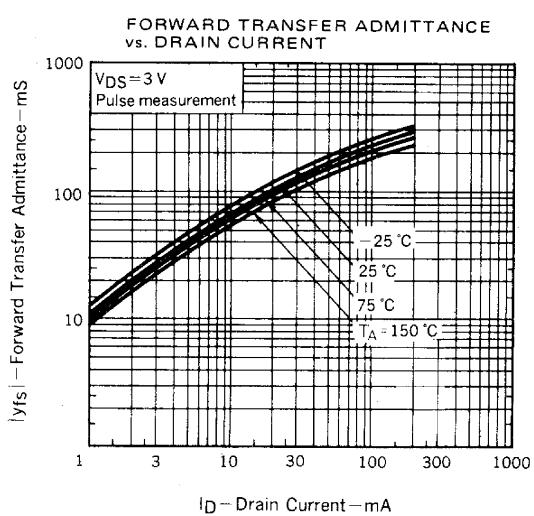
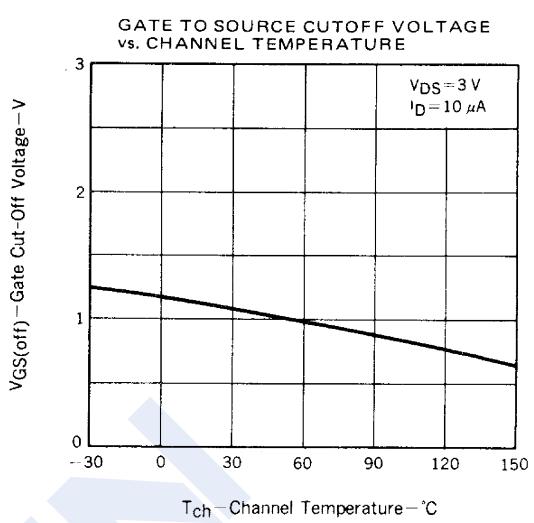
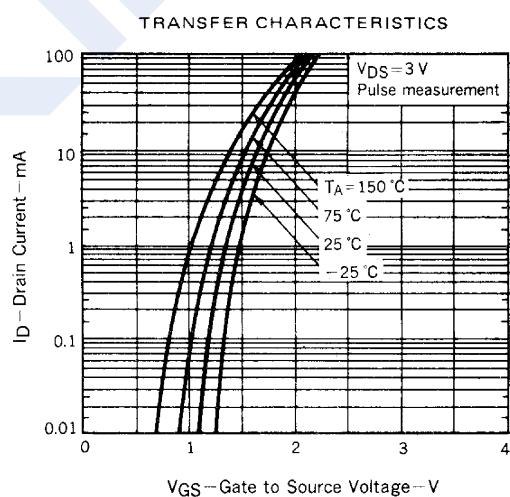
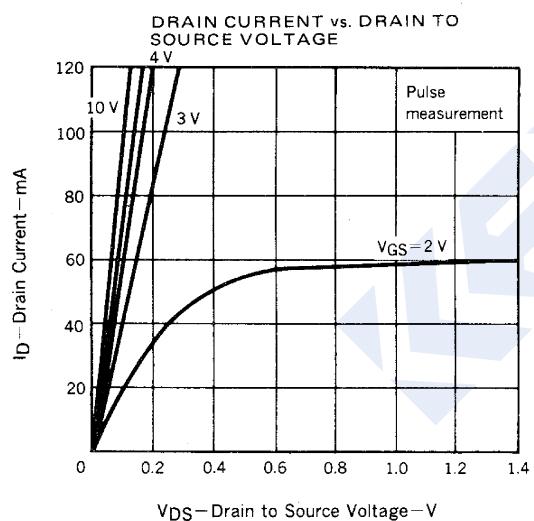
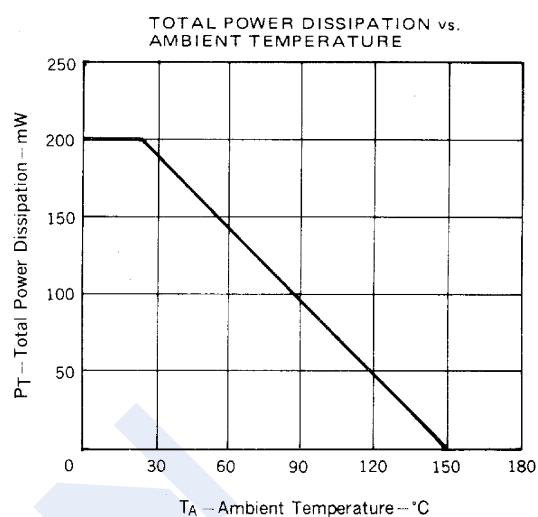
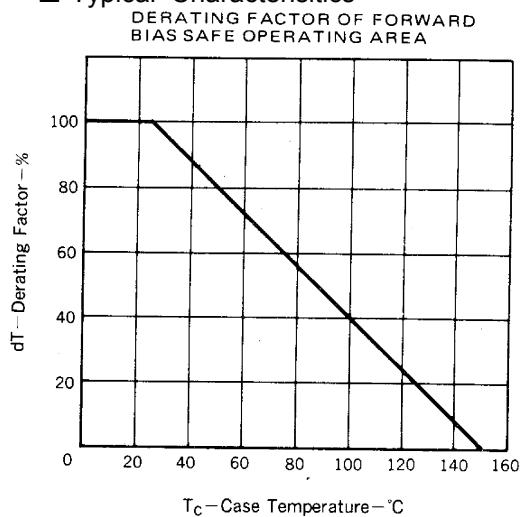
■ Marking

Marking	G14
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N-Channel MOSFET

2SK1581

■ Typical Characteristics

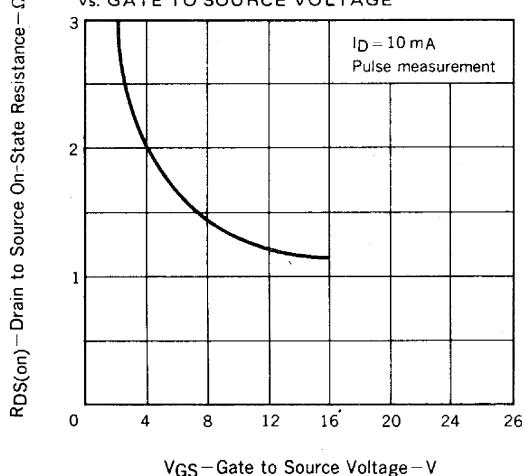


N-Channel MOSFET

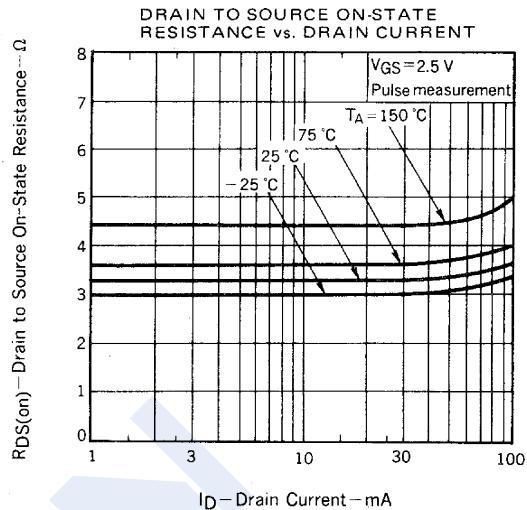
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■ Typical Characteristics

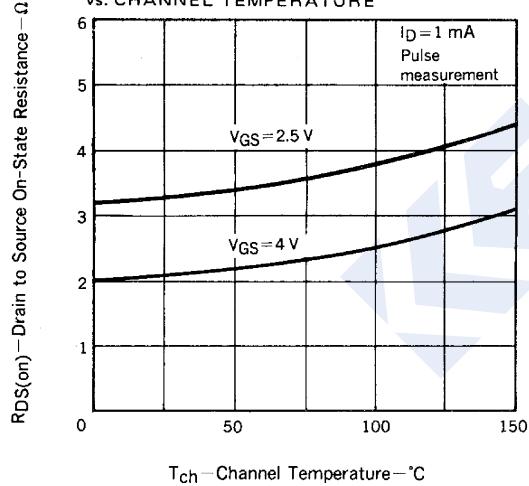
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



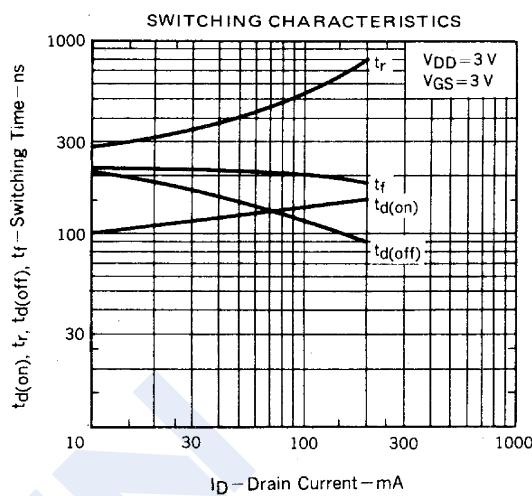
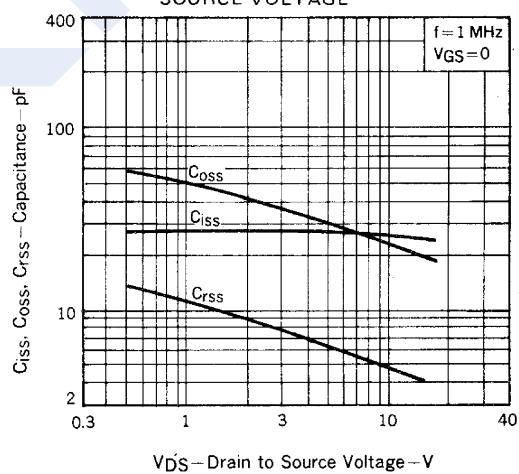
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

